NSN 5961-01-308-8620

Diode Semiconductor Device - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-308-8620

Inclosure Material:

Glass

Overall Length:

Between 0.120 inches and 0.300 inches

Terminal Length:

Between 1.000 inches and 1.500 inches

Overall Diameter:

Between 0.060 inches and 0.130 inches

Function For Which Designed:

Voltage reference

End Application:

6625-01-237-4658 test set, antenna drive

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

Do-7

Mounting Method:

Terminal

Features Provided:

Burn in and quality assurance level tx

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

6.4 regulator voltage

Voltage Tolerance In Percent:

-5.0/+5.0

Current Rating Per Characteristic:

60.00 milliamperes repetitive peak forward current

Power Rating Per Characteristic:

400.0 milliwatts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius junction

Precious Material And Location:

Terminal surface silver or terminal surface gold

Precious Material:

Silver or gold

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

2 uninsulated wire lead

Specification Data:

81349-mil-s-19500/452 government specification

Shelf Life:

N/a

NSN 5961-01-308-8620

Diode Semiconductor Device - Page 2 of 2



Unit Of Measure:

--

Demilitarization:

No

Fiig:

A110a0